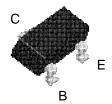


# FSB660 / FSB660A



SuperSOT<sup>™</sup>-3 (SOT-23)

# **PNP Low Saturation Transistor**

These devices are designed with high current gain and low saturation voltage with collector currents up to 2A continuous.

# **Absolute Maximum Ratings\*** $T_{A=25^{\circ}C \text{ unless otherwise noted}}$

Symbol	Parameter	FSB660/FSB660A	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current - Continuous	2	Α
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150°C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics T<sub>A = 25°C unless otherwise noted</sub>

Symbol	Characteristic	Max	Units
		FSB660/FSB660A	
P <sub>D</sub>	Total Device Dissipation	500	mW
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	250	°C/W

PNP LOW Saturation Transis	PNP	turation Transisto
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(continued)

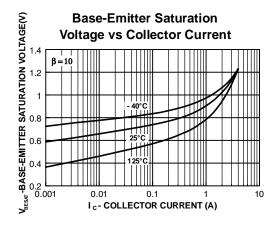
### **Electrical Characteristics**

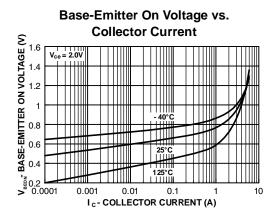
T<sub>A = 25°C</sub> unless otherwise noted

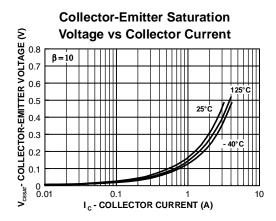
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAI	RACTERISTICS				
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10 mA	60		V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 100 μA	60		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 100 μA	5		V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 30 V		100	nA
		V <sub>CB</sub> = 30 V, T <sub>A</sub> =100°C		10	uA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V		100	nA
ON CHAR	ACTERISTICS*				
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 2 V	70		-
		I <sub>C</sub> =500mA, V <sub>CE</sub> =2V <b>FSB660</b>	100	300	
		FSB660A	250	550	
		I <sub>C</sub> = 1 A, V <sub>CE</sub> = 2 V	80		
		I <sub>C</sub> = 2 A, V <sub>CE</sub> = 2 V	40		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1 A, I <sub>B</sub> = 100 mA		300	mV
02(001)		I <sub>C</sub> = 2 A, I <sub>B</sub> =200 mA <b>FSB660</b>		350	
		FSB660A		300	
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1 A, I <sub>B</sub> = 100 mA		1.25	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 1 A, V <sub>CE</sub> = 2 V		1	V
SMALL SI	GNAL CHARACTERISTICS			•	•
C <sub>obo</sub>	Output Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1MHz		30	pF
f <sub>T</sub>	Transition Frequency	I <sub>C</sub> = 100 mA,V <sub>CE</sub> = 5 V, f=100MHz	75		-
	1			1	

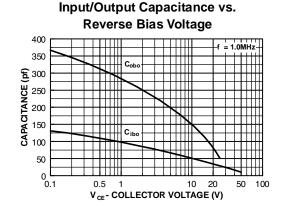
\*Pulse Test: Pulse Width  $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%$ 

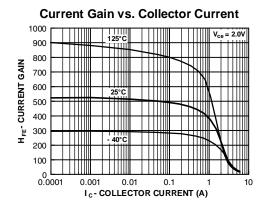
# **Typical Characteristics**











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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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